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Quad 2-Input NOR Gate

High-Performance Silicon-Gate CMOS

Features

- Outputs Source/Sink 24 mA
- 'ACT02 Has TTL Compatible Inputs
- These are Pb–Free Devices

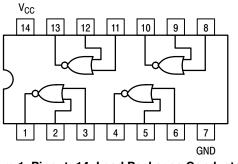
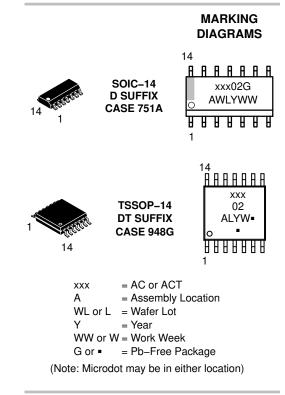


Figure 1. Pinout: 14–Lead Packages Conductors (Top View)



ON Semiconductor®

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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		$-0.5 \leq V_I \leq V_{CC} + 0.5$	V
V _O	DC Output Voltage	(Note 1)	$-0.5 \leq V_O \leq V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current		±20	mA
I _{OK}	DC Output Diode Current		± 50	mA
I _O	DC Output Sink/Source Current		± 50	mA
I _{CC}	DC Supply Current per Output Pin		± 50	mA
I _{GND}	DC Ground Current per Output Pin		± 50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10) Seconds	260	°C
TJ	Junction temperature under Bias		+ 150	°C
θ_{JA}	Thermal Resistance (Note 2)	SOIC TSSOP	125 170	°C/W
P _D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	125 170	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Ch	Human Body Model (Note 3) Machine Model (Note 4) harged Device Model (Note 5)	> 2000 > 200 > 1000	V
I _{Latch-Up}	Latch–Up Performance Above V _{CC} and	Below GND at 85°C (Note 6)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Io absolute maximum rating must be observed.
 The package thermal impedance is calculated in accordance with JESD51–7.
 Tested to EIA/JESD22–A114–A.

4. Tested to EIA/JESD22-A115-A.

Tested to JESD22-C101-A. 5.

6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Тур	Max	Unit	
N	Oursely Maltana	′AC	2.0	5.0	6.0	V	
V _{CC}	Supply Voltage	′ACT	4.5	5.0	5.5	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Ref. to GND)		0	-	V _{CC}	V	
		V _{CC} @ 3.0 V	-	150	-		
t _r , t _f	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	-	ns/V	
		V _{CC} @ 5.5 V	-	25	-		
	Input Rise and Fall Time (Note 2)	V _{CC} @ 4.5 V	-	10	-	20/1	
t _r , t _f	'ACT Devices except Schmitt Inputs	V _{CC} @ 5.5 V	-	8.0	-	ns/V	
TJ	Junction Temperature (PDIP)		_	-	140	°C	
T _A	Operating Ambient Temperature Range		-40	25	85	°C	
I _{OH}	Output Current – High		-	-	-24	mA	
I _{OL}	Output Current – Low		-	-	24	mA	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability. 1. V_{in} from 30% to 70% V_{CC} ; see individual Data Sheets for devices that differ from the typical input rise and fall times. 2. V_{in} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

	Parameter		74	AC	74AC		
Symbol		V _{CC} (V)	T _A = +25°C		T _A = -40°C to +85°C	Unit	Conditions
			Тур	Guar	anteed Limits		
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	v	$V_{OUT} = 0.1 V$ or $V_{CC} - 0.1 V$
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	v	$V_{OUT} = 0.1 V$ or $V_{CC} - 0.1 V$
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	v	l _{OUT} = –50 μA
		3.0 4.5 5.5		2.56 3.86 4.86	2.46 3.76 4.76	v	$V_{IN} = V_{IL} \text{ or } V_{IH}$ -12 mA I_{OH} -24 mA -24 mA
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	v	l _{OUT} = 50 μA
		3.0 4.5 5.5		0.36 0.36 0.36	0.44 0.44 0.44	v	$V_{IN} = V_{IL} \text{ or } V_{IH}$ 12 mA I_{OL} 24 mA 24 mA
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_{I} = V_{CC}, \text{ GND}$
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	-75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	-	4.0	40	μΑ	$V_{IN} = V_{CC}$ or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. *All outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time. NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V_{CC}.

AC CHARACTERISTICS

				74AC		74	AC		
Symbol	Parameter	V _{CC} * (V)	T, C	₄ = +25° L = 50 p	C F	T _A = - to +8 C _L = 9	35°C	Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay	3.3 5.0	1.5 1.5	5.0 4.0	7.5 6.0	1.0 1.0	8.0 6.5	ns	3–5
t _{PHL}	Propagation Delay	3.3 5.0	1.5 1.5	5.0 4.5	7.5 6.5	1.0 1.0	8.0 7.0	ns	3–5

*Voltage Range 3.3 V is 3.3 V ± 0.3 V. Voltage Range 5.0 V is 5.0 V ± 0.5 V.

DC CHARACTERISTICS

	Parameter		74ACT T _A = +25°C		74ACT	Unit		
Symbol		V _{CC} (V)			T _A = –40°C to +85°C		Conditions	
			Тур	Guar	anteed Limits			
V _{IH}			2.0 2.0	V	$V_{OUT} = 0.1 V$ or $V_{CC} - 0.1 V$			
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	v	$V_{OUT} = 0.1 V$ or $V_{CC} - 0.1 V$	
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = -50 μA	
		4.5 5.5		3.86 4.86	3.76 4.76	v	$V_{IN} = V_{IL} \text{ or } V_{IH}$ -24 mA I_{OH} -24 mA	
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	l _{OUT} = 50 μA	
		4.5 5.5		0.36 0.36	0.44 0.44	v	$V_{IN} = V_{IL} \text{ or } V_{IH}$ 24 mA I_{OL} 24 mA	
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μA	$V_{I} = V_{CC}, \text{ GND}$	
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	-	1.5	mA	$V_{I} = V_{CC} - 2.1 V$	
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max	
I _{OHD}	Output Current	5.5	-	-	-75	mA	V _{OHD} = 3.85 V Min	
I _{CC}	Maximum Quiescent Supply Current	5.5	-	4.0	40	μΑ	$V_{IN} = V_{CC} \text{ or } GND$	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. *All outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS

				74ACT		74 A	СТ		
Symbol	Parameter	V _{CC} * (V)	T, C	T _A = +25°C C _L = 50 pF		$T_{A} = -40^{\circ}C$ to +85°C C _L = 50 pF		Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay	5.0	1.5	-	8.5	1.0	9.0	ns	3–6
t _{PHL}	Propagation Delay	5.0	1.5	-	9.5	1.0	10	ns	3–6

*Voltage Range 5.0 V is 5.0 V ± 0.5 V.

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	30	pF	V _{CC} = 5.0 V

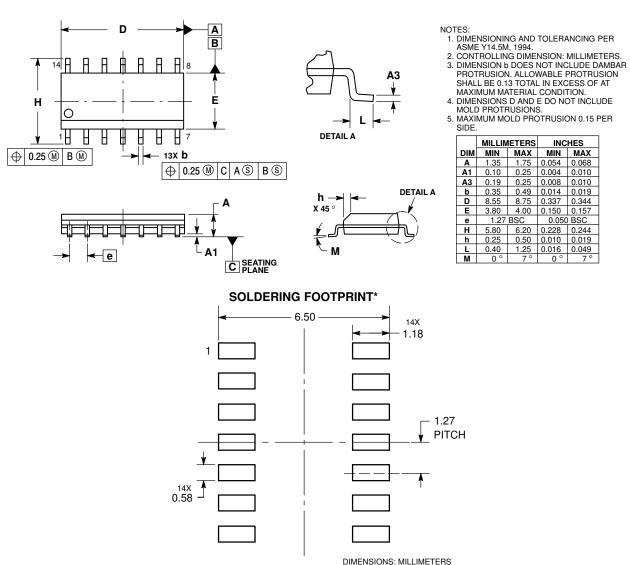
DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]		
MC74AC02DG	SOIC-14 (Pb-Free)	55 Units / Rail		
MC74AC02DR2G	SOIC-14 (Pb-Free) 2500 / Tape			
MC74ACT02DG	SOIC-14 (Pb-Free)	55 Units / Rail		
MC74ACT02DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel		
MC74AC02DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel		
MC74ACT02DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

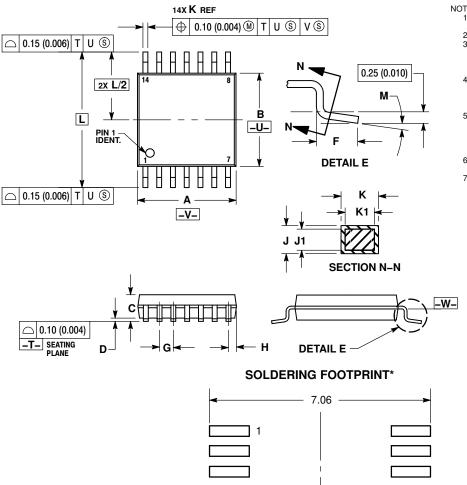
SOIC-14 NB CASE 751A-03 ISSUE K



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G **ISSUE B**

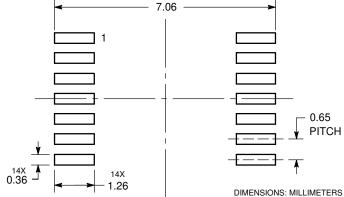


NOTES:

- DTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. S. DIMENSION K DOES NOT INCLUDE DAMBA

- NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE W–.

	MILLIN	IETERS	INCHES				
DIM	MIN MAX		MIN	MAX			
Α	4.90	5.10	0.193	0.200			
В	4.30	4.50	0.169	0.177			
С		1.20		0.047			
D	0.05 0.15		0.002	0.006			
F	0.50	0.75	0.020	0.030			
G	0.65	BSC	0.026 BSC				
Н	0.50	0.60	0.020	0.024			
J	0.09	0.20	0.004	0.008			
J1	0.09	0.16	0.004	0.006			
Κ	0.19	0.30	0.007	0.012			
K1	0.19	0.25	0.007	0.010			
L	6.40 BSC		0.252 BSC				
М	1 0° 8°		0 °	8 °			



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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